

# P-Channel 100 V (D-S) MOSFET

PRODUCT SUMMARY						
V <sub>DS</sub> (V)	$R_{DS(on)}(\Omega)$ Max.	I <sub>D</sub> (A)	Q <sub>g</sub> (Typ.)			
- 100	$0.214 \text{ at V}_{GS} = -10 \text{ V}$	- 18	37			
- 100	$0.221$ at $V_{GS} = -4.5 \text{ V}$	- 14	37			

# FEATURESDT-Trench



• DT-Trench Power MOSFET

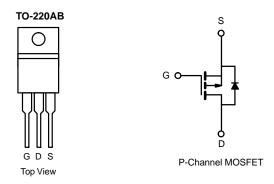
• 100 % R<sub>g</sub> and UIS Tested

• Compliant to RoHS Directive 2002/95/EC

# RoHS

#### **APPLICATIONS**

- Power Switch
- Load Switch in High Current Applications
- DC/DC Converters



<b>ABSOLUTE MAXIMUM RATINGS</b> (T <sub>C</sub> = 25 °C, unless otherwise noted)						
Parameter	Symbol	Limit	Unit			
Drain-Source Voltage	V <sub>DS</sub>	- 100	V			
Gate-Source Voltage	V <sub>GS</sub>	± 20	v			
Continuous Drain Current (T <sub>.1</sub> = 150 °C)	T <sub>C</sub> = 25 °C	1-	- 18	A		
Continuous Diain Current (1) = 130 C)	T <sub>C</sub> = 70 °C	⊢ I <sub>D</sub> ⊢	- 13			
Pulsed Drain Current (t = 300 μs)	I <sub>DM</sub>	- 100				
Avalanche Current	I <sub>AS</sub>	- 10				
Single Avalanche Energy <sup>a</sup>	L = 0.1 mH	E <sub>AS</sub>	31	mJ		
Mariana Bana Biasingian	T <sub>C</sub> = 25 °C	D	11.7 <sup>b</sup>	W		
Maximum Power Dissipation <sup>a</sup>	T <sub>A</sub> = 25 °C <sup>c</sup>	P <sub>D</sub>	1.1			
Operating Junction and Storage Temperature Range		T <sub>J</sub> , T <sub>sta</sub>	- 55 to 150	°C		

THERMAL RESISTANCE RATINGS					
Parameter	Symbol	Limit	Unit		
Junction-to-Ambient (PCB Mount) <sup>c</sup>	R <sub>thJA</sub>	60	°C/W		
Junction-to-Case (Drain)	R <sub>thJC</sub>	9	C/VV		

#### Notes:

- a. Duty cycle  $\leq$  1 %.
- b. See SOA curve for voltage derating.
- c. When mounted on 1" square PCB (FR-4 material).



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Parameter	Symbol	Test Conditions	Min.	Тур.	Max.	Unit	
Static							
Drain-Source Breakdown Voltage	V <sub>DS</sub>	$V_{DS} = 0 \text{ V}, I_{D} = -250 \mu\text{A}$	- 100		V		
Gate Threshold Voltage	V <sub>GS(th)</sub>	$V_{DS} = V_{GS}, I_{D} = -250 \mu A$	- 1		- 3.5	V	
Gate-Body Leakage	I <sub>GSS</sub>	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$	V <sub>GS</sub> = ± 20 V		± 250	nA	
		V <sub>DS</sub> = - 60 V, V <sub>GS</sub> = 0 V			- 1		
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> = - 100 V, V <sub>GS</sub> = 0 V, T <sub>J</sub> = 125 °C			- 50		
		V <sub>DS</sub> = - 100 V, V <sub>GS</sub> = 0 V, T <sub>J</sub> = 150 °C			- 250		
On-State Drain Current <sup>a</sup>	I <sub>D(on)</sub>	$V_{DS} \le -10 \text{ V}, V_{GS} = -10 \text{ V}$	- 18			Α	
	D	V <sub>GS</sub> = - 10 V, I <sub>D</sub> = - 14 A		0.214		Ω	
Drain-Source On-State Resistance <sup>a</sup>	R <sub>DS(on)</sub>	V <sub>GS</sub> = - 4.5 V, I <sub>D</sub> = - 12 A		0.221			
Forward Transconductance <sup>a</sup>	9 <sub>fs</sub>	V <sub>DS</sub> = - 20 V, I <sub>D</sub> = - 14 A		20		S	
Dynamic <sup>b</sup>							
Input Capacitance	C <sub>iss</sub>			1765		pF	
Output Capacitance	C <sub>oss</sub>	$V_{GS} = 0 \text{ V}, V_{DS} = -20 \text{ V}, f = 1 \text{ MHz}$		330			
Reverse Transfer Capacitance	C <sub>rss</sub>	1		280			
Total Gate Charge <sup>c</sup>	$Q_g$			67	100		
Gate-Source Charge <sup>c</sup>	$Q_{gs}$	$V_{DS} = -20 \text{ V}, V_{GS} = -10 \text{ V}, I_{D} = -14 \text{ A}$		13.5		nC	
Gate-Drain Charge <sup>c</sup>	$Q_{gd}$	1		14		1	
Gate Resistance	R <sub>g</sub>	f = 1 MHz	0.5	2.5	5	Ω	
Turn-On Delay Time <sup>c</sup>	t <sub>d(on)</sub>			10	20		
Rise Time <sup>c</sup>	t <sub>r</sub>	$V_{DD}$ = - 20 V, $R_L$ = 2 $\Omega$		11	20	- ns	
Turn-Off Delay Time <sup>c</sup>	t <sub>d(off)</sub>	$I_D \cong$ - 10 A, $V_{GEN}$ = - 10 V, $R_g$ = 1 $\Omega$		42	63		
Fall Time <sup>c</sup>	t <sub>f</sub>	1		12	20		
Drain-Source Body Diode Ratings ar	nd Characteri	stics T <sub>C</sub> = 25 °C <sup>b</sup>					
Continuous Current	Is				- 18	^	
Pulsed Current	I <sub>SM</sub>				- 100	_ A	
Forward Voltage <sup>a</sup>	V <sub>SD</sub>	I <sub>F</sub> = - 10 A, V <sub>GS</sub> = 0 V		- 0.8	- 1.5	V	
Reverse Recovery Time	t <sub>rr</sub>			38	57	ns	
Peak Reverse Recovery Current	I <sub>RM(REC)</sub>	I <sub>F</sub> = - 10 A, dI/dt = 100 A/μs		2.3	3.5	Α	
Reverse Recovery Charge	Q <sub>rr</sub>	1		40	60	nC	

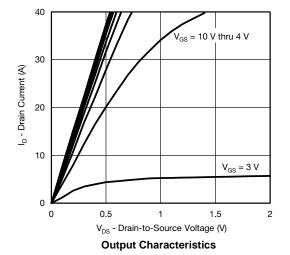
#### Notes:

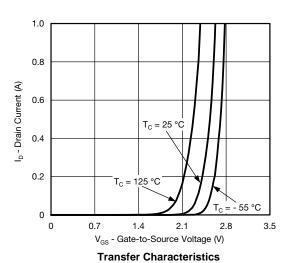
- a. Pulse test; pulse width  $\leq 300~\mu s,$  duty cycle  $\leq 2~\%.$  b. Guaranteed by design, not subject to production testing.
- c. Independent of operating temperature.

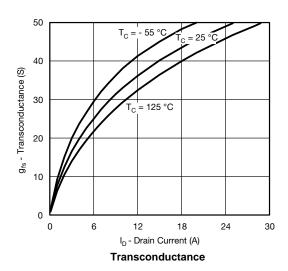
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

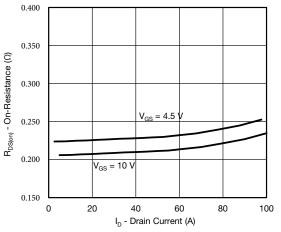


#### TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

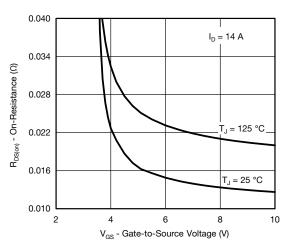




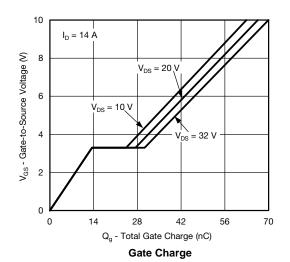




**On-Resistance vs. Drain Current** 

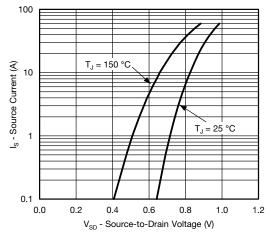


On-Resistance vs. Gate-to-Source Voltage

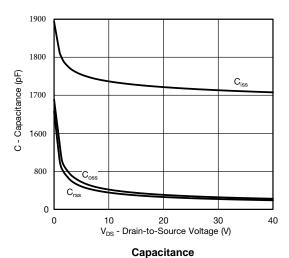




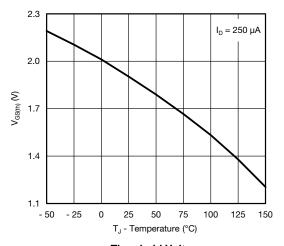
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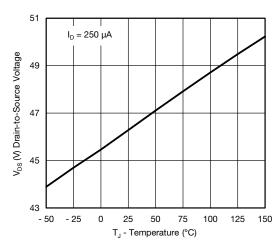
Source-Drain Diode Forward Voltage



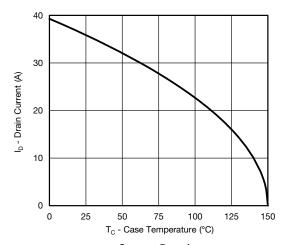
On-Resistance vs. Junction Temperature



**Threshold Voltage** 



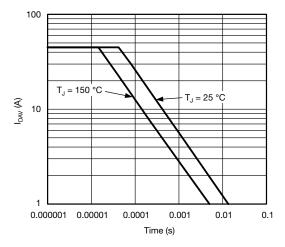
Drain Source Breakdown vs. Junction Temperature



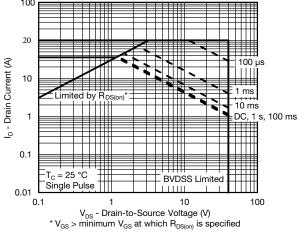
**Current Derating** 



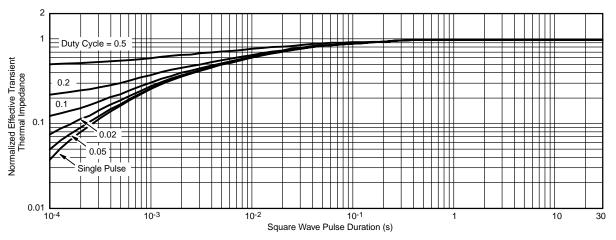
#### TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



Single Pulse Avalanche Current Capability vs. Time



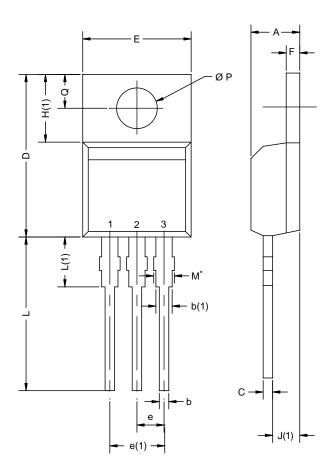
Safe Operating Area



Normalized Thermal Transient Impedance, Junction-to-Case



## **TO-220AB**



	MILLIMETERS		INCHES	
DIM.	MIN.	MAX.	MIN.	MAX.
Α	4.25	4.65	0.167	0.183
b	0.69	1.01	0.027	0.040
b(1)	1.20	1.73	0.047	0.068
С	0.36	0.61	0.014	0.024
D	14.85	15.49	0.585	0.610
Е	10.04	10.51	0.395	0.414
е	2.41	2.67	0.095	0.105
e(1)	4.88	5.28	0.192	0.208
F	1.14	1.40	0.045	0.055
H(1)	6.09	6.48	0.240	0.255
J(1)	2.41	2.92	0.095	0.115
L	13.35	14.02	0.526	0.552
L(1)	3.32	3.82	0.131	0.150
ØΡ	3.54	3.94	0.139	0.155
Q	2.60	3.00	0.102	0.118
ECN: X12-0208-Rev. N, 08-Oct-12 DWG: 5471				

#### Notes

 $<sup>^{*}</sup>$  M = 1.32 mm to 1.62 mm (dimension including protrusion) Heatsink hole for HVM





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